



# FDD8647L

## N-Channel PowerTrench<sup>®</sup> MOSFET

40 V, 42 A, 9 mΩ

### Features

- Max  $r_{DS(on)}$  = 9 mΩ at  $V_{GS} = 10$  V,  $I_D = 13$  A
- Max  $r_{DS(on)}$  = 13 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 11$  A
- Fast Switching
- 100% UIL tested
- RoHS Compliant

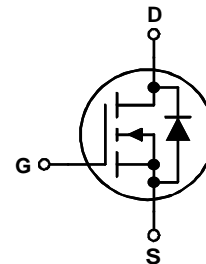
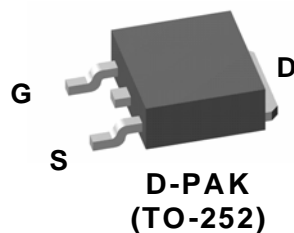


### General Description

This N-Channel MOSFET has been produced using Fairchild Semiconductor's proprietary PowerTrench<sup>®</sup> technology to deliver low  $r_{DS(on)}$  and optimized  $BV_{DSS}$  capability to offer superior performance benefit in the application.

### Applications

- Inverter
- Power Supplies



### MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	40	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	42	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	52	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	14	
	-Pulsed	100	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	33	mJ
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$	43	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	3.1	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.9	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	40	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8647L	FDD8647L	D-PAK (TO-252)	13 "	16 mm	2500 units

**Electrical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		31		mV/ $^{\circ}\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	1.0	2.0	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		-6		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 13\text{ A}$		7.1	9.0	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 11\text{ A}$		9.9	13.0	
		$V_{GS} = 10\text{ V}$ , $I_D = 13\text{ A}$ , $T_J = 125\text{ }^{\circ}\text{C}$		10.7	13.6	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}$ , $I_D = 13\text{ A}$		49		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		1230	1640	pF
$C_{oss}$	Output Capacitance			340	455	pF
$C_{rss}$	Reverse Transfer Capacitance			55	80	pF
$R_g$	Gate Resistance			0.9		$\Omega$

**Switching Characteristics**

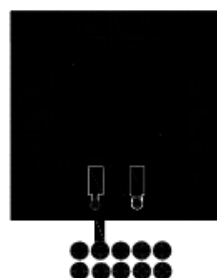
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20\text{ V}$ , $I_D = 13\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		8	16	ns
$t_r$	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	34	ns
$t_f$	Fall Time			2	10	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to }10\text{ V}$	$V_{DD} = 20\text{ V}$ , $I_D = 13\text{ A}$	20	28	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V to }4.5\text{ V}$		10	14	nC
$Q_{gs}$	Gate to Source Charge			3.8		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			3.1		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 2.6\text{ A}$ (Note 2)		0.75	1.2	V
		$V_{GS} = 0\text{ V}$ , $I_S = 13\text{ A}$ (Note 2)		0.84	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 13\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		28	45	ns
$Q_{rr}$	Reverse Recovery Charge			15	27	nC

**Notes:**

1:  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  
 $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a)  $40\text{ }^{\circ}\text{C/W}$  when mounted on a  
1 in<sup>2</sup> pad of 2 oz copper



b)  $96\text{ }^{\circ}\text{C/W}$  when mounted on  
a minimum pad

2: Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3: Starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 0.3\text{ mH}$ ,  $I_{AS} = 15.0\text{ A}$ ,  $V_{DD} = 36\text{ V}$ ,  $V_{GS} = 10.0\text{ V}$ .

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

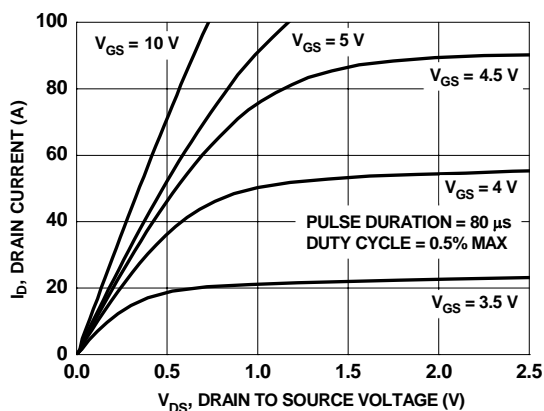


Figure 1. On Region Characteristics

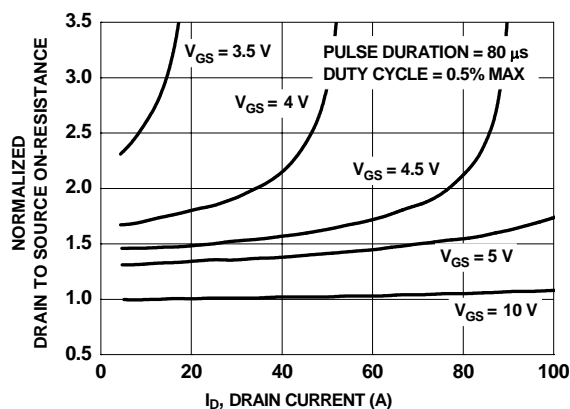


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

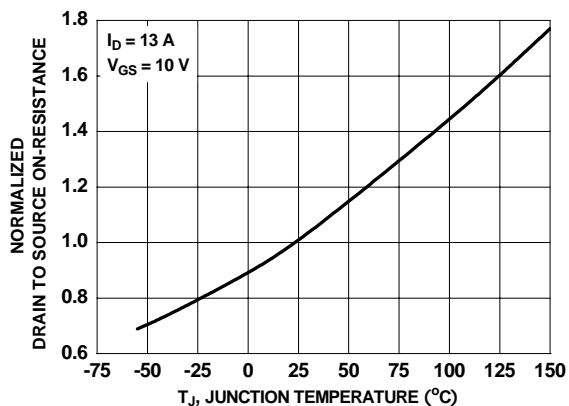


Figure 3. Normalized On Resistance vs Junction Temperature

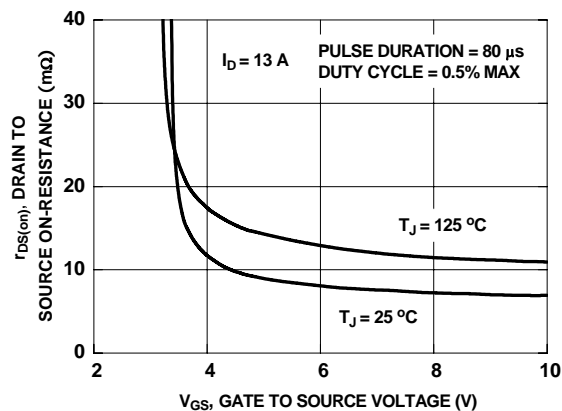


Figure 4. On-Resistance vs Gate to Source Voltage

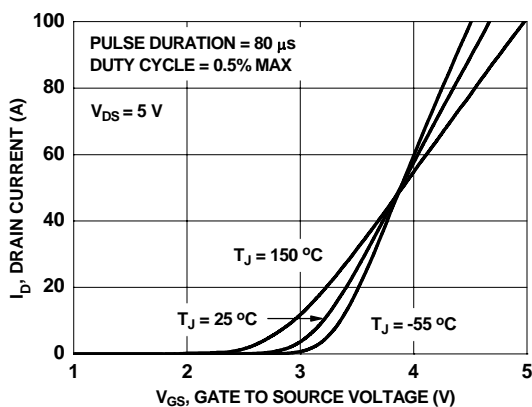


Figure 5. Transfer Characteristics

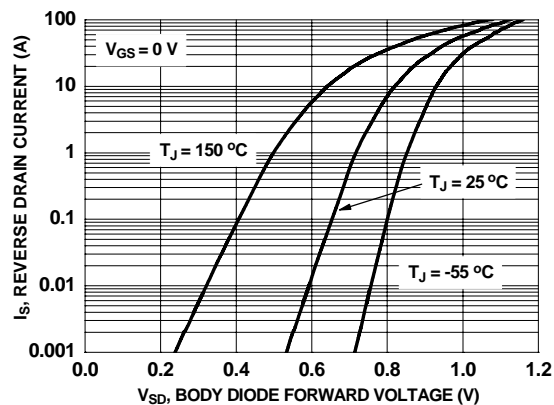


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

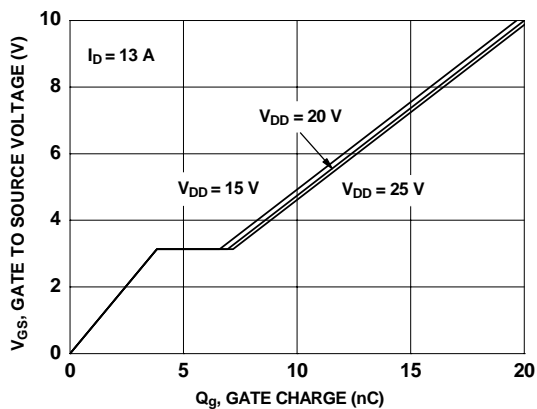


Figure 7. Gate Charge Characteristics

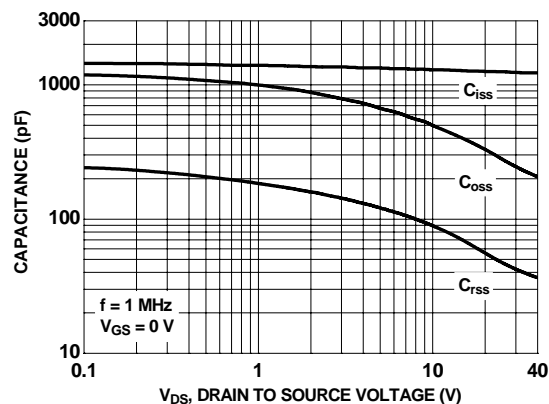


Figure 8. Capacitance vs Drain to Source Voltage

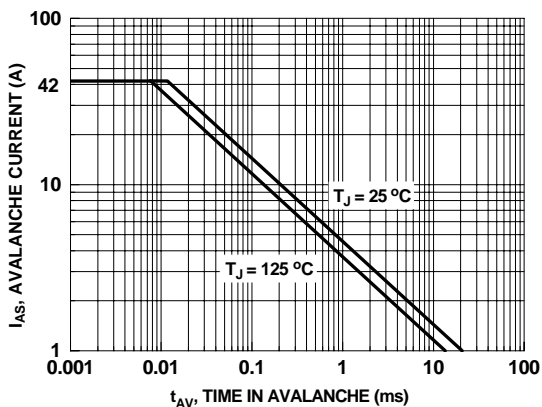


Figure 9. Unclamped Inductive Switching Capability

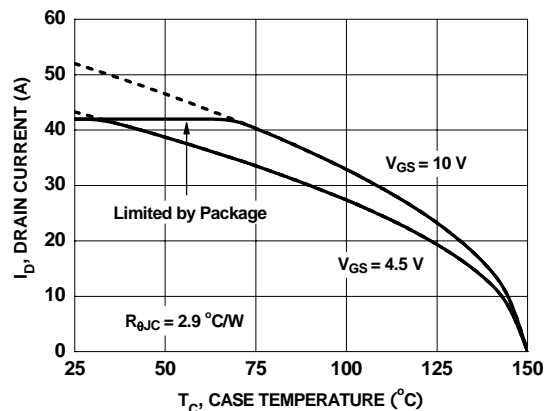


Figure 10. Maximum Continuous Drain Current vs Case Temperature

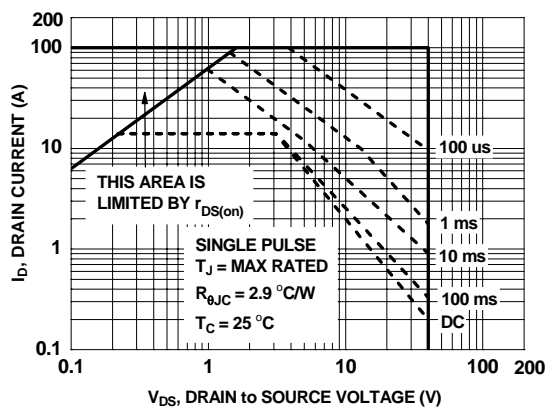


Figure 11. Forward Bias Safe Operating Area

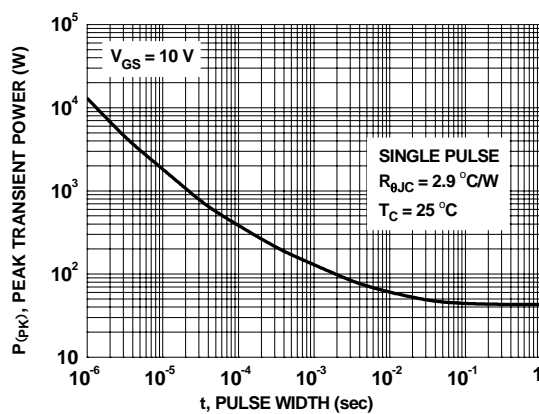
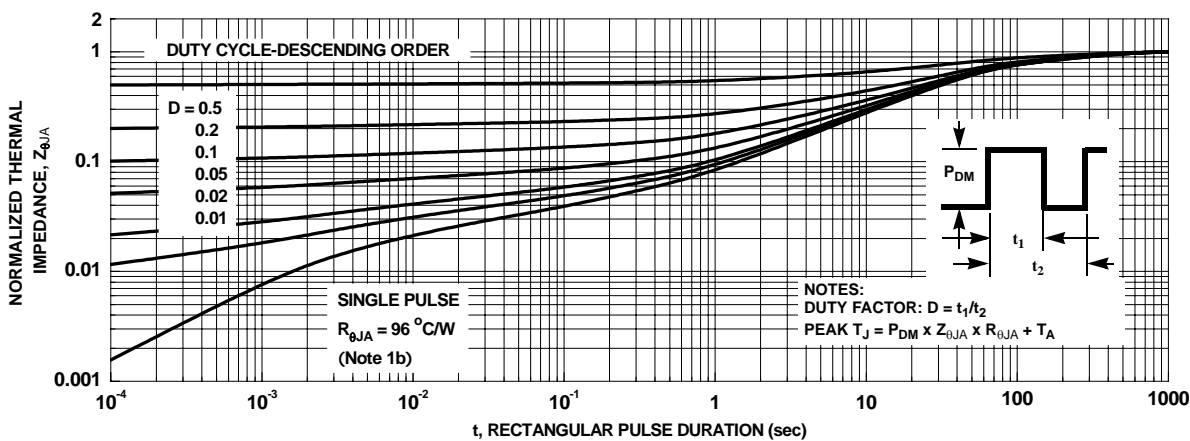
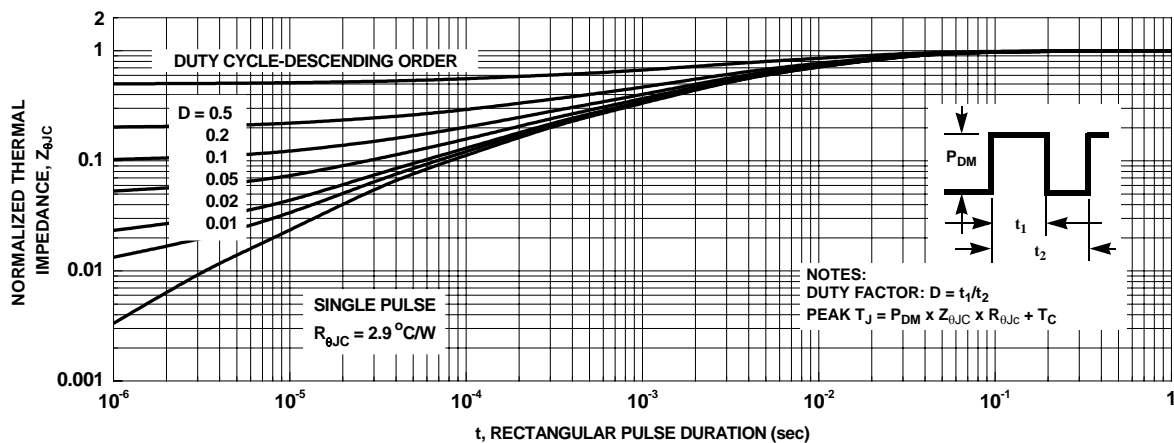
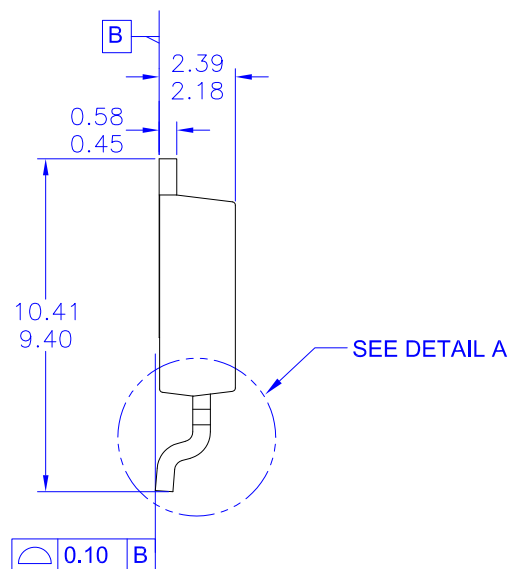
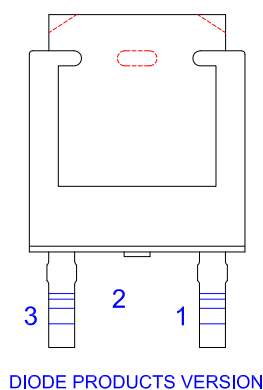
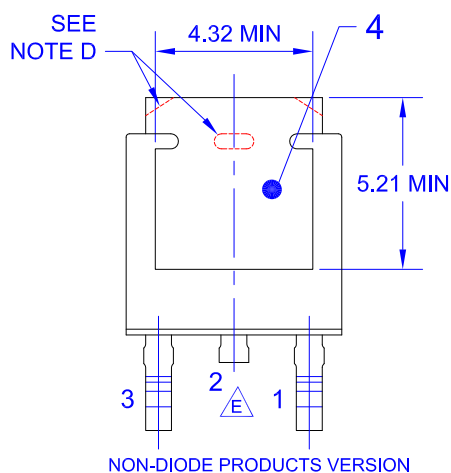
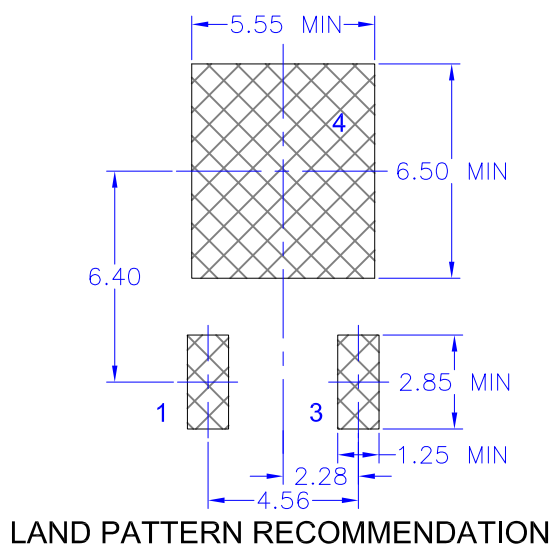
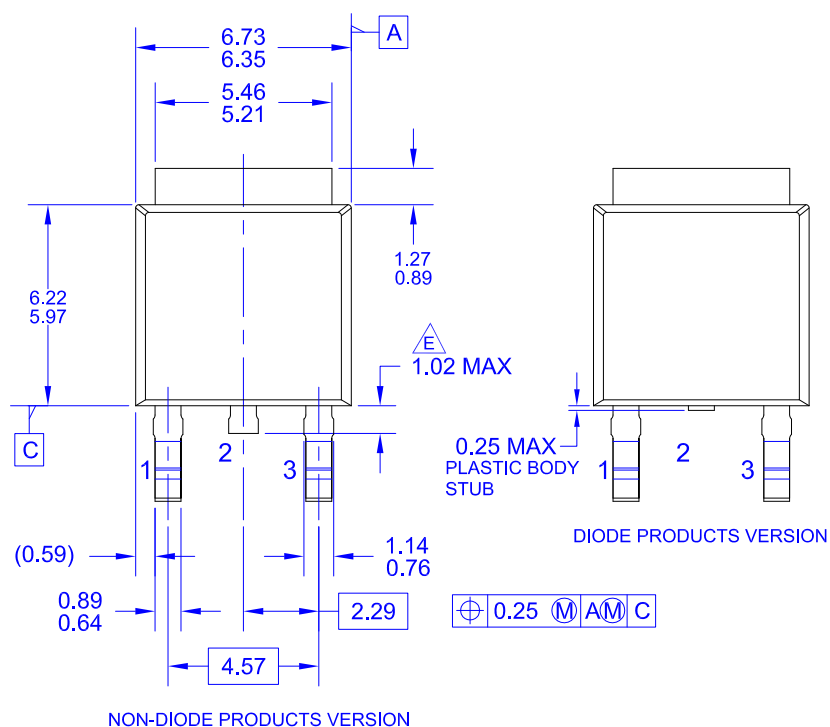


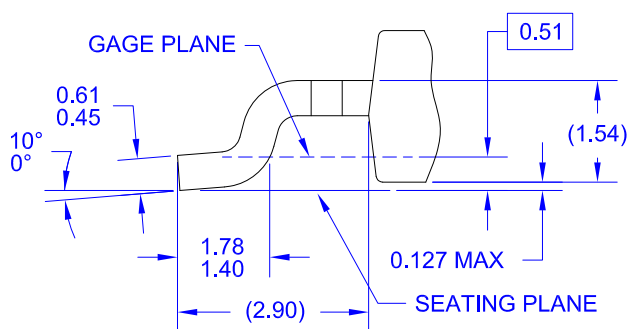
Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted





- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
  - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
  - E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
  - F) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
  - H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV10





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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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Rev. I74

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401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd  
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➤ Sales :

Direct     +86 (21) 6401-6692  
  
Email       amall@ameya360.com  
  
QQ         800077892  
  
Skype       ameyasales1 ameyasales2

➤ Customer Service :

Email       service@ameya360.com

➤ Partnership :

Tel         +86 (21) 64016692-8333  
  
Email       mkt@ameya360.com